

What Is Claimed Is:

1. A method for fabricating an RF semiconductor device comprising:

forming a trench to define an active region and an element isolation region in a semiconductor substrate;

forming at least one gate line within the active region of the semiconductor substrate, the at least one gate line not extending over a center of the trench;

forming an insulating layer on the at least one gate line and the semiconductor substrate;

forming a contact hole in the insulating layer;

forming a contact plug in the contact hole; and

forming a conductive pattern layer electrically connected with the contact plug.

2. A method as defined in claim 1, wherein the at least one gate line comprises at least two gate lines, and the at least two gate lines are not connected with each other in the element isolation region

3. A method as defined in claim 2 wherein at least two of the at least two gate lines are connected in the active region.

4. A method as defined in claim 1, wherein a thickness of the insulating layer is about 1000 to about 20000 angstroms.

5. A method as defined in claim 1, wherein a thickness of the conductive pattern layer is above 10000 angstroms.

6. A method as defined in claim 1, wherein the insulating layer is one of a low temperature oxide and a polyimide.

7. A method as defined in claim 1, wherein the at least one gate line is formed in order to minimize parasitic capacitance between the at least one gate line and the substrate.

8. A method as defined in claim 1, wherein the at least one gate line is formed in order to minimize resistance of the at least one gate line.

9. A method as defined in claim 1, furthur comprising metal contacts linking at least two of the at least one gate lines.

10. A method as defined in claim 1, wherein the at least one gate line does not extend along a longitudinal axis of the trench.

11. An RF semiconductor device comprising:
a substrate having an active region and an isolation region; and
a plurality of gate lines formed in the active region but not in the isolation region of the substrate.

12. A semiconductor device as defined in claim 11 further comprising:
a trench formed in the substrate, wherein at least one of the gate lines does not extend over a center of the trench.